

/ Descriptions

WO0220I ММ Ё NPN æ Ñ ç s ll 1 Silicon NPN transistor in a TO-220F Plastic Package.

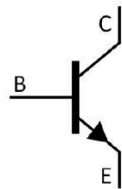
/ Features

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High breakdown voltage, low collector output capacitance, wide SOA.

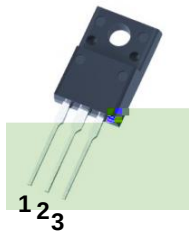
/ Applications

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Ideal for Color TV chroma output and amplification of video signals.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

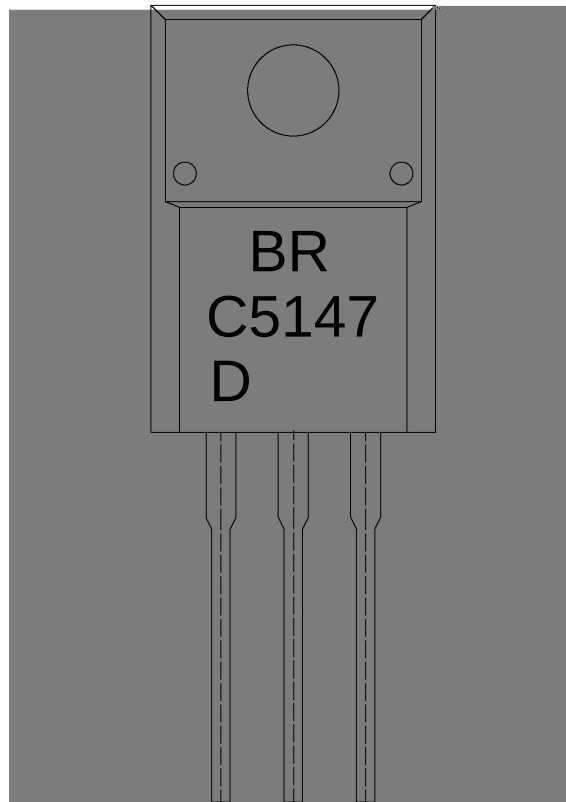
/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	D	E
h _{FE} Range	60 120	100 200

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ C)$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=50\mu A$ $I_E=0$	300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=100\mu A$ $I_B=0$	300			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=50\mu A$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=200V$ $I_B=0$			0.5	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=4.0V$ $I_B=0$			0.5	μA
DC Current Gain	h_{FE}	$V_{CE}=10V$ $I_C=10mA$	60		200	

/ Marking Instructions



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Note:

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$$h_{FE} \approx 6 \text{ dB}$$

$\mathbb{H} \mid f \check{n} \quad \Gamma_b \quad \mid \mathfrak{e} \mid f \check{n} \quad \Psi \rho$

Company Code.

Product Type.

h_{FE} Classifications Symbol

Lot No. Code, code change with Lot No.

